

top gate

V_{tg}

Al₂O₃

($\epsilon_r=9.1$)

$E_{Al_2O_3}$

$d_{Al_2O_3}$

top hBN

($\epsilon_r=4$)

E_t

d_t

top graphene

V_t

middle hBN

($\epsilon_r=4$)

E_{gg}

d_{gg}

bottom graphene

V_b

bottom hBN

($\epsilon_r=4$)

E_b

d_b

bottom gate

V_{bg}

